



ZVN4525Z

N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

V _{(BR)DSS}	R _{DS(ON)}	Ι _D Τ _A = +25°C		
250V	8.5Ω @ V _{GS} = 10V	240mA		

Description

This new generation MOSFET is designed to minimize the on-state resistance ($R_{DS(ON)}$) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Applications

- Power Management Functions
- Battery Operated Systems and Solid-State Relays
- Drivers: Relays, Solenoids, Lamps, Hammers, Displays, Memories, Transistors, etc

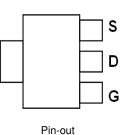
Features

- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)

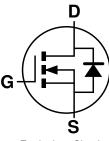
Mechanical Data

- Case: SOT89
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Finish Annealed over Copper Lead frame. Solderable per MIL-STD-202, Method 208 @3
- Weight: 0.052 grams (Approximate)





Top View



Equivalent Circuit

Ordering Information (Note 4)

Part Number	Compliance	Case	Quantity per Reel
ZVN4525ZTA	Standard	SOT89	1,000

1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.

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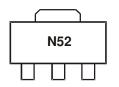
2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information

Notes:



N52 = Marking Code



Maximum Ratings (@ $T_A = +25^{\circ}C$, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
Drain-Source Voltage			V _{DSS}	250	V
Gate-Source Voltage			V _{GSS}	±40	V
Continuous Drain Current, V _{GS} = 10V	Steady State	$T_A = +25^{\circ}C \text{ (Note 5)}$ $T_A = +70^{\circ}C \text{ (Note 5)}$	ID	240 192	mA
Maximum Body Diode Forward Current			Is	1.1	A
Pulsed Drain Current (Note 7)			IDM	1.44	A
Pulsed Source Current (Note 7)			I _{SM}	1.44	А

Thermal Characteristics

Characteristic	Symbol	Value	Unit	
Total Power Dissipation Linear Derating Factor	T _A = +25°C (Note 5)	P _D	1.2 9.6	W mW/°C
Thermal Resistance, Junction to Ambient	Steady State (Note 5)	Peri	103	°C/W
	Steady State (Note 6)	R _{0JA}	50	°C/W
Operating and Storage Temperature Range	T _{J,} T _{STG}	-55 to +150	°C	

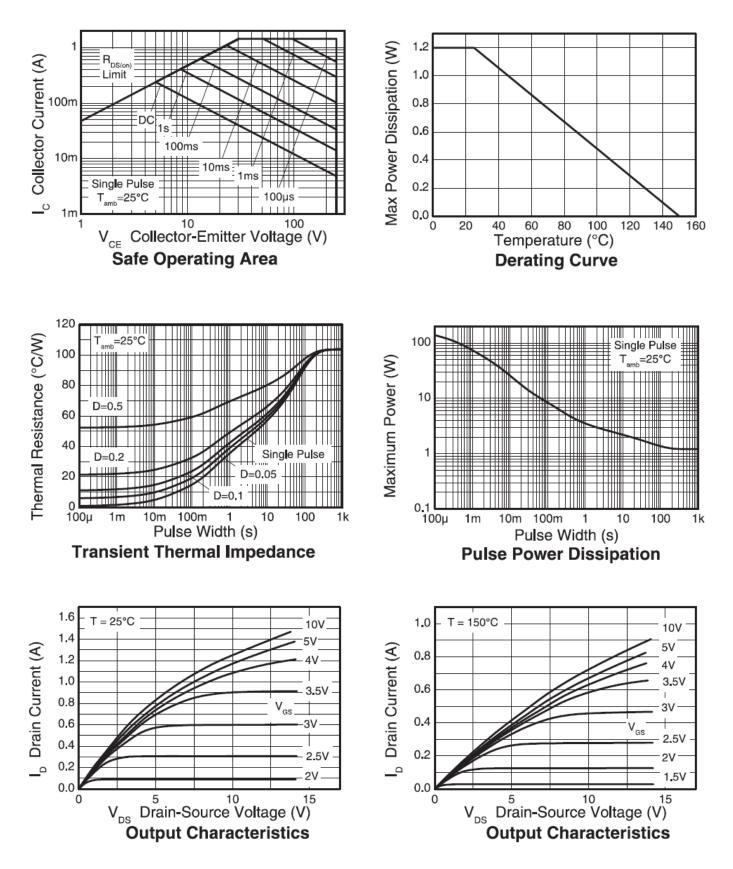
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 9)			•	•		•	
Drain-Source Breakdown Voltage	BV _{DSS}	250	285	—	V	$V_{GS} = 0V, I_D = 1mA$	
Zero Gate Voltage Drain Current	I _{DSS}	_	35	500	nA	$V_{DS} = 250V, V_{GS} = 0V$	
Gate-Source Leakage	IGSS		±1	±100	nA	$V_{GS} = \pm 40V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 9)			•	•		•	
Gate Threshold Voltage	V _{GS(TH)}	0.8	1.4	1.8	V	$V_{DS} = V_{GS}, I_D = 1mA$	
		_	5.6	8.5		$V_{GS} = 10V, I_D = 500mA$	
Static Drain-Source On-Resistance (Note 8)	R _{DS(ON)}	_	5.9	9.0	Ω	$V_{GS} = 4.5V, I_D = 360mA$	
			6.4	9.5		$V_{GS} = 2.4V, I_D = 20mA$	
Diode Forward Voltage (Note 8)	V _{SD}		_	0.97	V	$V_{GS} = 0V, I_S = 360mA$	
Forward Transconductance (Note 10)	g fs	0.3	475	—	S	$V_{DS} = 10V, I_D = 0.3A$	
DYNAMIC CHARACTERISTICS (Note 10)			•	•		•	
Input Capacitance	Ciss		72			$V_{DS} = 25V, V_{GS} = 0V$ f = 1.0MHz	
Output Capacitance	Coss	_	11	—	pF		
Reverse Transfer Capacitance	Crss	_	3.6	—			
Total Gate Charge	Qg	_	2.6	3.65			
Gate-Source Charge	Q _{gs}		0.2	0.28	nC	$V_{DS} = 25V, I_D = 360mA, V_{GS} = 10V$	
Gate-Drain Charge	Q _{gd}		0.5	0.70			
Turn-On Delay Time	t _{D(ON)}		1.25				
Turn-On Rise Time	t _R	_	1.70	—	ns	$V_{DD} = 50V, R_G = 6.0\Omega,$	
Turn-Off Delay Time	t _{D(OFF)}	_	11.40	—	115	$I_D = 200 \text{mA}, R_D = 4.4 \Omega$	
Turn-Off Fall Time	tF	_	3.50				
Body Diode Reverse Recovery Time	t _{RR}		186	260	ns	I⊧ = 360mA. dl/dt = 100A/µs	
Body Diode Reverse Recovery Charge	Q _{RR}	_	34	48	nC	F = 300 mA, u/u = 100 A/ µs	

Notes: 5. For a device surface mounted on 25mm X 25mm FR-4 PCB with high coverage of single sided 1oz copper, in still air condition.

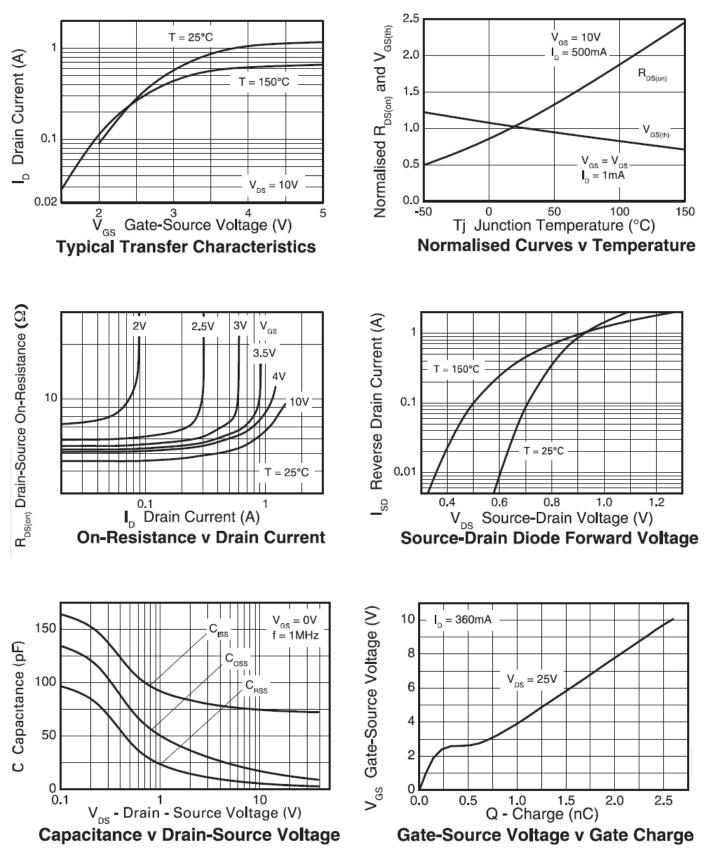
For a device surface mounted on 251mm x251mm re-4 PCB with light coverage of single sided 102 cf.
For a device surface mounted on FR4 PCB measured at t ≤5 secs.
Repetitive rating - pulse width limited by maximum junction temperature. Refer to Transient Thermal.
Measured under pulsed conditions. Width=300µs. Duty cycle ≤ 2%.
Short duration pulse test used to minimize self-heating effect.
Guaranteed by design. Not subject to product testing.





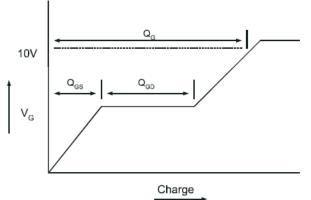


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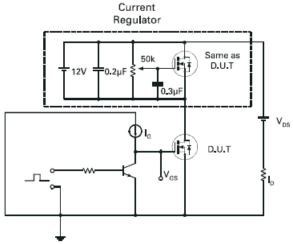




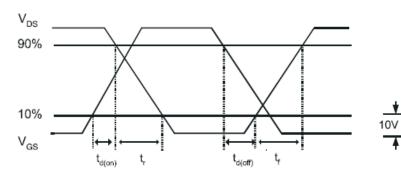
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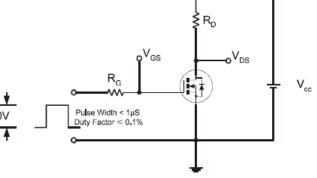
Basic Gate Charge Waveform



Gate Charge Test Circuit



Switching Time Waveforms

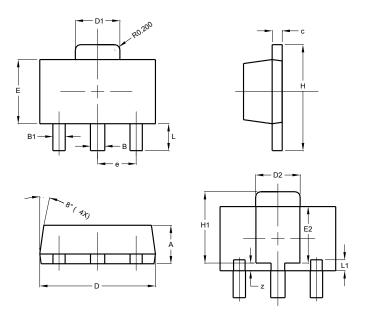


Switching Time Test Circuit



Package Outline Dimensions

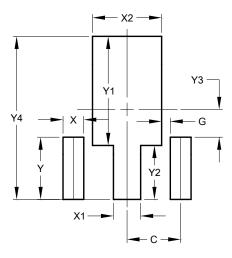
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.



	SOT89					
Dim	Min	Max	Тур			
Α	1.40	1.60	1.50			
В	0.50	0.62	0.56			
B1	0.42	0.54	0.48			
С	0.35	0.43	0.38			
D	4.40	4.60	4.50			
D1	1.62	1.83	1.733			
D2	1.61	1.81	1.71			
Е	2.40	2.60	2.50			
E2	2.05	2.35	2.20			
е	-	-	1.50			
Н	3.95	4.25	4.10			
H1	2.63	2.93	2.78			
L	0.90	1.20	1.05			
L1	0.427 REF					
Z	0.30 REF					
All	All Dimensions in mm					

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)		
С	1.500		
G	0.244		
Х	0.580		
X1	0.760		
X2	1.933		
Y	1.730		
Y1	3.030		
Y2	1.500		
Y3	0.770		
Y4	4.530		



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